

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> MAX	I <sub>D</sub> MAX T <sub>C</sub> = +25°C
100V	30mΩ @ V <sub>GS</sub> = 10V	26A
	50mΩ @ V <sub>GS</sub> = 4.5V	21A

## Description

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- Backlighting
- Power management functions
- DC-DC converters

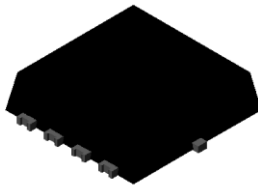
## Features and Benefits

- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Wettable Flank for Improved Optical Inspection
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **The DIODES™ DMTH10H032LFVWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**  
<https://www.diodes.com/quality/product-definitions/>

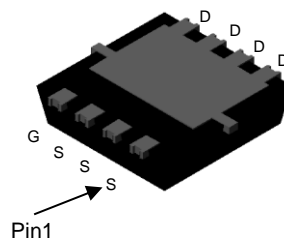
## Mechanical Data

- Package: PowerDI®3333-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.072 grams (Approximate)

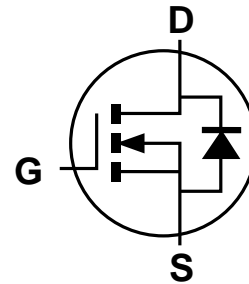
PowerDI3333-8 (SWP) (Type UX)



Top View



Bottom View



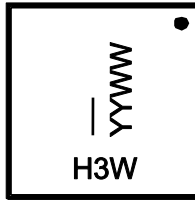
Equivalent Circuit

## Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMTH10H032LFVWQ-7	PowerDI3333-8 (SWP) (Type UX)	2,000	Tape and Reel
DMTH10H032LFVWQ-13	PowerDI3333-8 (SWP) (Type UX)	3,000	Tape and Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



H3W = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Two Digits of Year (ex: 22 = 2022)  
 WW = Week Code (01 to 53)

## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	100	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	I <sub>D</sub>	T <sub>C</sub> = +25°C	26
		T <sub>C</sub> = +100°C	18
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	104	A
Maximum Continuous Body Diode Forward Current (Note 5)	I <sub>S</sub>	26	A
Pulsed Body Diode Forward Current (Note 6)	I <sub>SM</sub>	104	A
Avalanche Current, L = 0.3mH (Note 6)	I <sub>AS</sub>	13	A
Avalanche Energy, L = 0.3mH (Note 6)	E <sub>AS</sub>	25.3	mJ

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 7)	P <sub>D</sub>	1.7	W
Thermal Resistance, Junction to Ambient (Note 7)	R <sub>θJA</sub>	90	°C/W
Total Power Dissipation (Note 8)	P <sub>D</sub>	3.8	W
Thermal Resistance, Junction to Ambient (Note 8)	R <sub>θJA</sub>	40	°C/W
Thermal Resistance, Junction to Case (Note 5)	R <sub>θJC</sub>	3.3	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

- Notes:
- Thermal resistance from junction to soldering point (on the exposed drain pad).
  - I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  - Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 9)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 9)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.3	—	2.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	22	30	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 10A
		—	32	50		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 5A
Diode Forward Voltage	V <sub>SD</sub>	—	0.8	1	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 6A
<b>DYNAMIC CHARACTERISTICS (Note 10)</b>						
Input Capacitance	C <sub>iSS</sub>	—	683	—	pF	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	165	—	pF	
Reverse Transfer Capacitance	C <sub>rSS</sub>	—	6.9	—	pF	
Gate Resistance	R <sub>g</sub>	—	1.2	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	6.3	—	nC	V <sub>DS</sub> = 50V, I <sub>D</sub> = 6A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	11.9	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	2.0	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	3.1	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	4.1	—	ns	V <sub>DS</sub> = 50V, R <sub>L</sub> = 5.85Ω V <sub>GS</sub> = 10V, R <sub>g</sub> = 3Ω
Turn-On Rise Time	t <sub>R</sub>	—	4.5	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	12.5	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	9.3	—	ns	
Reverse Recovery Time	t <sub>RR</sub>	—	31.5	—	ns	I <sub>F</sub> = 6A, di/dt = 500A/μs
Reverse Recovery Charge	Q <sub>RR</sub>	—	94.6	—	nC	

Notes: 9. Short duration pulse test used to minimize self-heating effect.  
10. Guaranteed by design. Not subject to product testing.

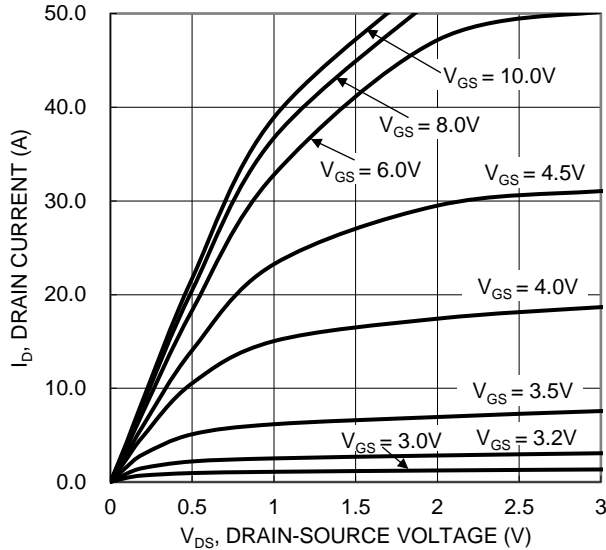


Figure 1. Typical Output Characteristic

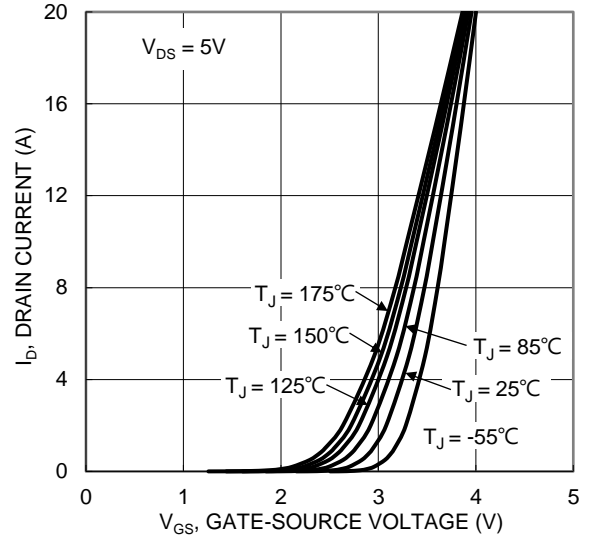


Figure 2. Typical Transfer Characteristic

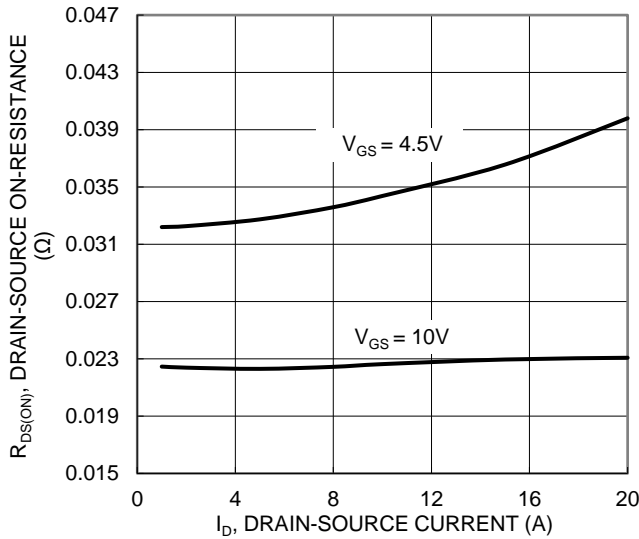


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

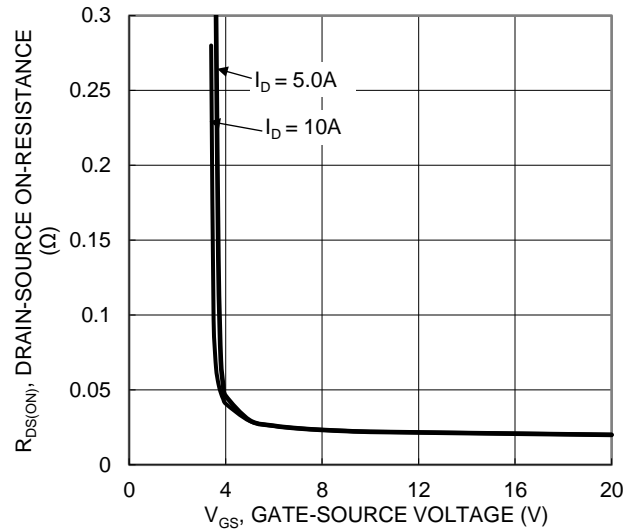


Figure 4. Typical Transfer Characteristic

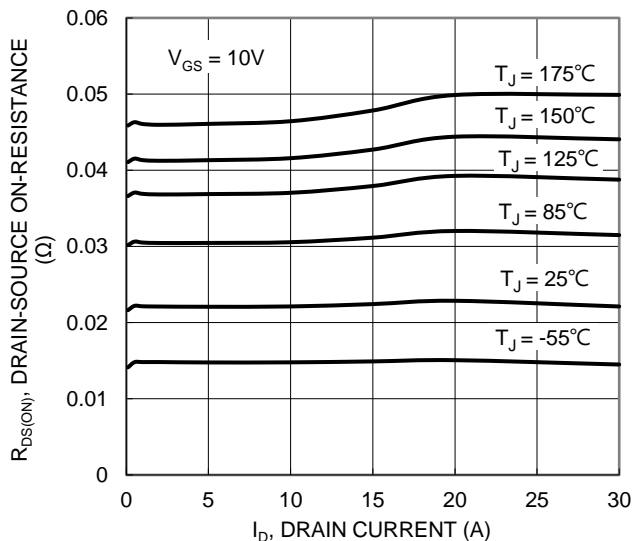


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

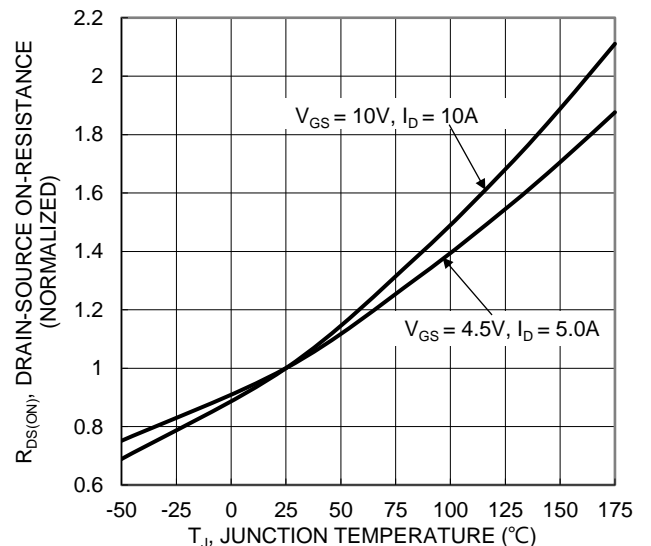


Figure 6. On-Resistance Variation with Temperature

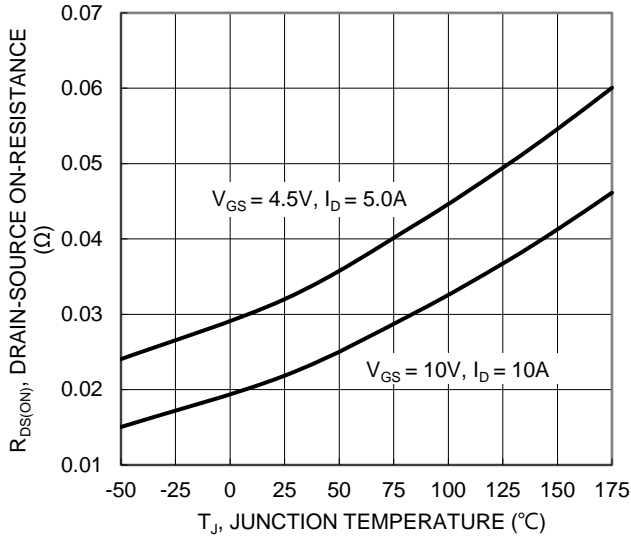


Figure 7. On-Resistance Variation with Temperature

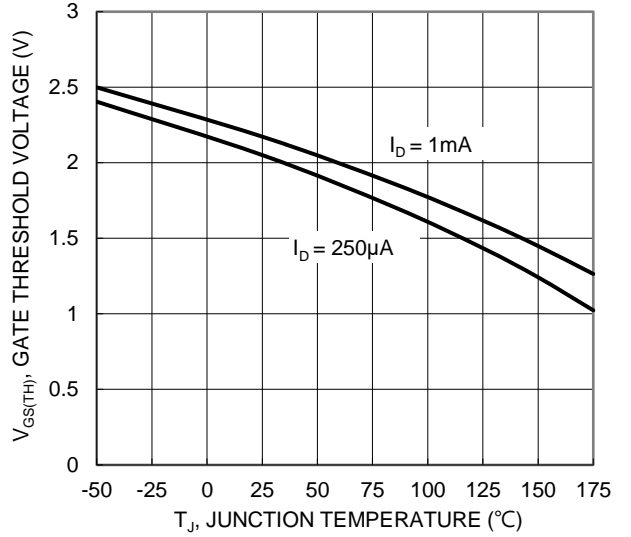


Figure 8. Gate Threshold Variation vs. Junction Temperature

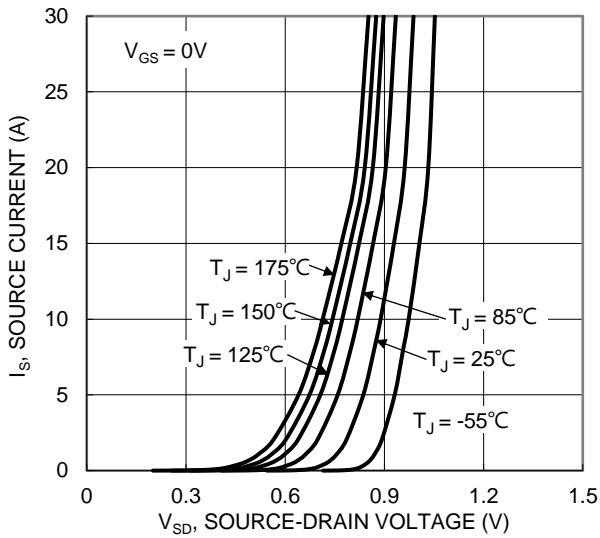


Figure 9. Diode Forward Voltage vs. Current

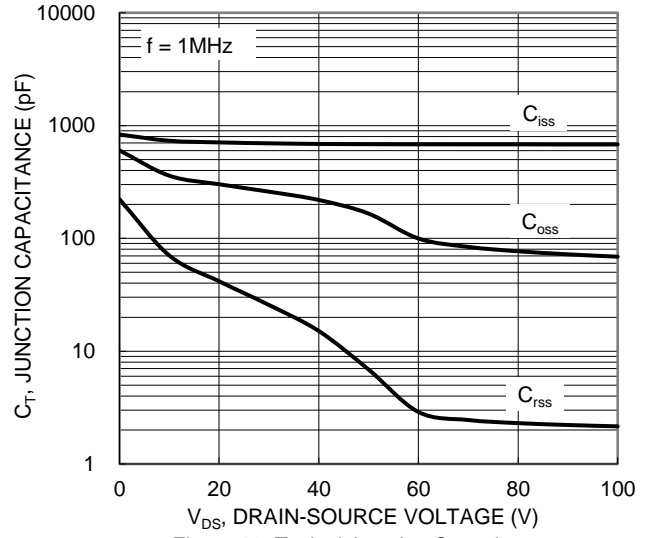


Figure 10. Typical Junction Capacitance

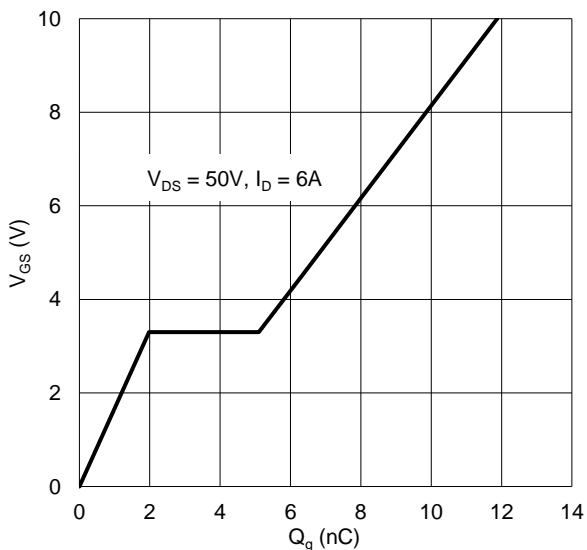


Figure 11. Gate Charge

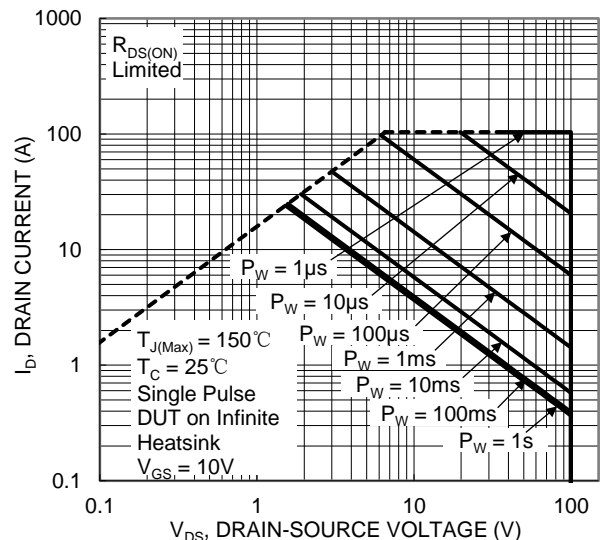


Figure 12. SOA, Safe Operation Area

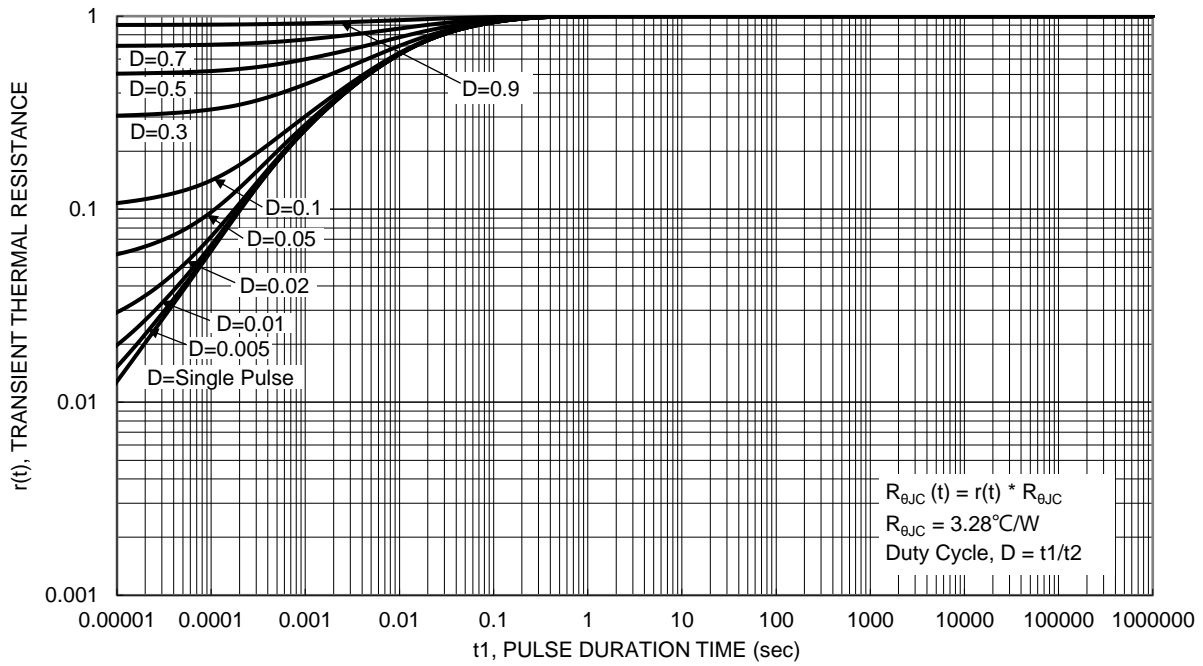
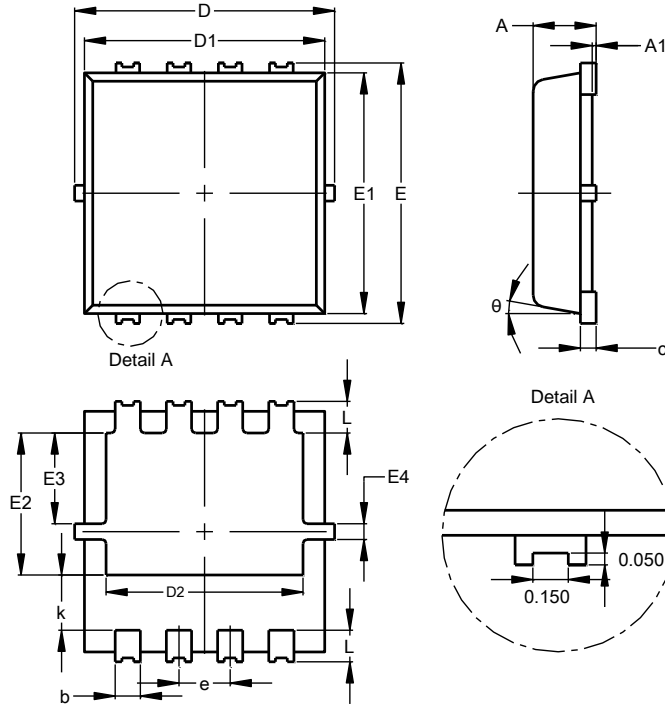


Figure 13. Transient Thermal Resistance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### PowerDI3333-8 (SWP) (Type UX)

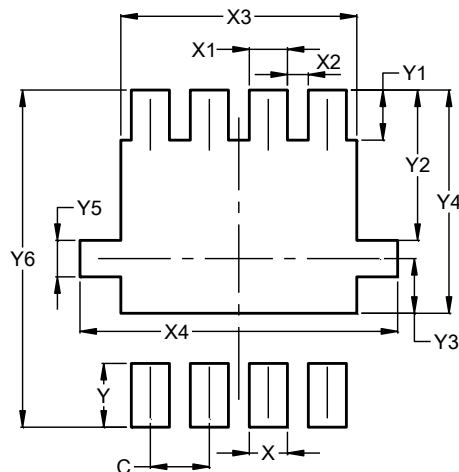


PowerDI3333-8 (SWP) (Type UX)			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	--
b	0.25	0.40	0.32
c	0.10	0.25	0.15
D	3.20	3.40	3.30
D1	2.95	3.15	3.05
D2	2.30	2.70	2.50
E	3.20	3.40	3.30
E1	2.95	3.15	3.05
E2	1.60	2.00	1.80
E3	0.95	1.35	1.15
E4	0.10	0.30	0.20
e	--	--	0.65
k	0.50	0.90	0.70
L	0.30	0.50	0.40
θ	0°	12°	10°
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700

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